Luca Francaviglia

List of Publications by Year in descending order

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840585 794469 25 363 11 19 citations h-index g-index papers 25 25 25 677 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Ag–Diamond Core–Shell Nanostructures Incorporated with Silicon-Vacancy Centers. ACS Materials Au, 2022, 2, 85-93.	2.6	3
2	Excitonic absorption and defect-related emission in three-dimensional MoS ₂ pyramids. Nanoscale, 2022, 14, 1179-1186.	2.8	3
3	Optimizing cathodoluminescence microscopy of buried interfaces through nanoscale heterostructure design. Nanoscale, 2022, 14, 7569-7578.	2.8	2
4	Autonomous scanning probe microscopy investigations over WS2 and Au $\{111\}$. Npj Computational Materials, 2022, 8, .	3.5	6
5	GaAs nanoscale membranes: prospects for seamless integration of Ill–Vs on silicon. Nanoscale, 2020, 12, 815-824.	2.8	12
6	Quantitative Nanoscale Absorption Mapping: A Novel Technique To Probe Optical Absorption of Two-Dimensional Materials. Nano Letters, 2020, 20, 567-576.	4.5	22
7	3D Ordering at the Liquid–Solid Polar Interface of Nanowires. Advanced Materials, 2020, 32, e2001030.	11.1	10
8	Formation, electronic structure, and optical properties of self-assembled quantum-dot single-photon emitters in Ga(N,As,P) nanowires. Physical Review Materials, 2020, 4, .	0.9	4
9	Increasing N content in GaNAsP nanowires suppresses the impact of polytypism on luminescence. Nanotechnology, 2019, 30, 405703.	1.3	6
10	Ill–V Integration on Si(100): Vertical Nanospades. ACS Nano, 2019, 13, 5833-5840.	7.3	24
11	Tuning adatom mobility and nanoscale segregation by twin formation and polytypism.		
	Nanotechnology, 2019, 30, 054006.	1.3	3
12	Nanotechnology, 2019, 30, 054006. Segregation scheme of indium in AlGalnAs nanowire shells. Physical Review Materials, 2019, 3, .	0.9	11
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	Nanotechnology, 2019, 30, 054006. Segregation scheme of indium in AlGalnAs nanowire shells. Physical Review Materials, 2019, 3, . Bistability of Contact Angle and Its Role in Achieving Quantum-Thin Self-Assisted GaAs nanowires.	0.9	11
13	Nanotechnology, 2019, 30, 054006. Segregation scheme of indium in AlGalnAs nanowire shells. Physical Review Materials, 2019, 3, . Bistability of Contact Angle and Its Role in Achieving Quantum-Thin Self-Assisted GaAs nanowires. Nano Letters, 2018, 18, 49-57. Anisotropic-Strain-Induced Band Gap Engineering in Nanowire-Based Quantum Dots. Nano Letters, 2018,	0.9	62
13	Nanotechnology, 2019, 30, 054006. Segregation scheme of indium in AlGalnAs nanowire shells. Physical Review Materials, 2019, 3, . Bistability of Contact Angle and Its Role in Achieving Quantum-Thin Self-Assisted GaAs nanowires. Nano Letters, 2018, 18, 49-57. Anisotropic-Strain-Induced Band Gap Engineering in Nanowire-Based Quantum Dots. Nano Letters, 2018, 18, 2393-2401. Optimizing the yield of A-polar GaAs nanowires to achieve defect-free zinc blende structure and	0.9 4.5 4.5	11 62 10
13 14 15	Nanotechnology, 2019, 30, 054006. Segregation scheme of indium in AlGalnAs nanowire shells. Physical Review Materials, 2019, 3, . Bistability of Contact Angle and Its Role in Achieving Quantum-Thin Self-Assisted GaAs nanowires. Nano Letters, 2018, 18, 49-57. Anisotropic-Strain-Induced Band Gap Engineering in Nanowire-Based Quantum Dots. Nano Letters, 2018, 18, 2393-2401. Optimizing the yield of A-polar GaAs nanowires to achieve defect-free zinc blende structure and enhanced optical functionality. Nanoscale, 2018, 10, 17080-17091. Dopant-Induced Modifications of Ga⟨i⟩⟨sub⟩⟨li>In⟨sub⟩⟨lia⟩(1â€"⟨i⟩x⟨lio⟩⟨sub⟩P Nanowire-Based pâ€"n Junctions Monolithically Integrated on Si(111). ACS Applied Materials & Contact Cont	0.9 4.5 4.5	11 62 10 31

#	Article	IF	CITATION
19	Surface passivation and self-regulated shell growth in selective area-grown GaN–(Al,Ga)N core–shell nanowires. Nanoscale, 2017, 9, 7179-7188.	2.8	21
20	Nanoporous silicon tubes: the role of geometry in nanostructure formation and application to light emitting diodes. Journal Physics D: Applied Physics, 2017, 50, 265101.	1.3	1
21	Quantum Dots in Nanowires. Semiconductors and Semimetals, 2016, , 159-184.	0.4	3
22	Strain-Induced Band Gap Engineering in Selectively Grown GaN–(Al,Ga)N Core–Shell Nanowire Heterostructures. Nano Letters, 2016, 16, 7098-7106.	4.5	41
23	Quantum dots in the GaAs/Al <i>\times</i> Ga1â^' <i>\times</i> As core-shell nanowires: Statistical occurrence as a function of the shell thickness. Applied Physics Letters, 2015, 107, .	1.5	13
24	Three-dimensional nanoscale study of Al segregation and quantum dot formation in GaAs/AlGaAs core-shell nanowires. Applied Physics Letters, 2014, 105, .	1.5	45
25	10.1063/1.4904952.1., 2014, , .		0